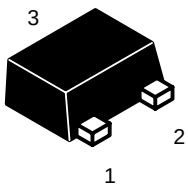
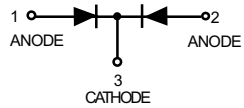
SCHOTTKY BARRIER DIODE

LRB715WT1



SC-89



●Features

Small surface mounting type SC-89

Low V_F and low I_R

High reliability

●Construction

silicon epitaxial planar

MAXIMUM RATINGS (T_A = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Peak forward surge current*	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 ⌓

DEVICE MARKING

LRB715WT1=3D

ELECTRICAL CHARACTERISTICS(T_A=25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.37	V	I_F=1mA
Reverse current	I_R	–	–	1	μA	V_R=10V
Capacitance between terminals	C_T	–	2.0	–	pF	V_R=1V,f=1MHz

LRB715WT1

Electrical characteristic curves(T_A = 25°C)

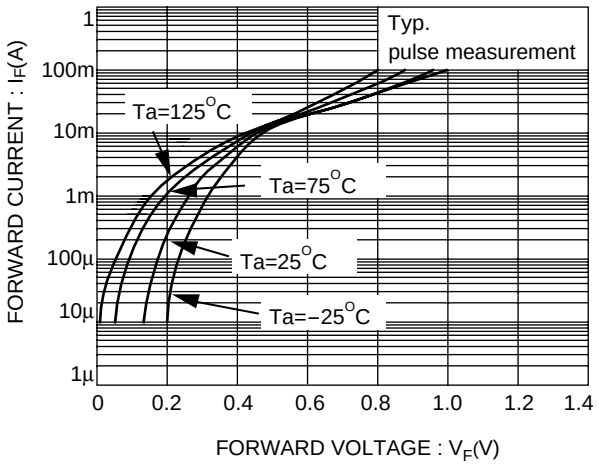


Fig. 1 Forward characteristics

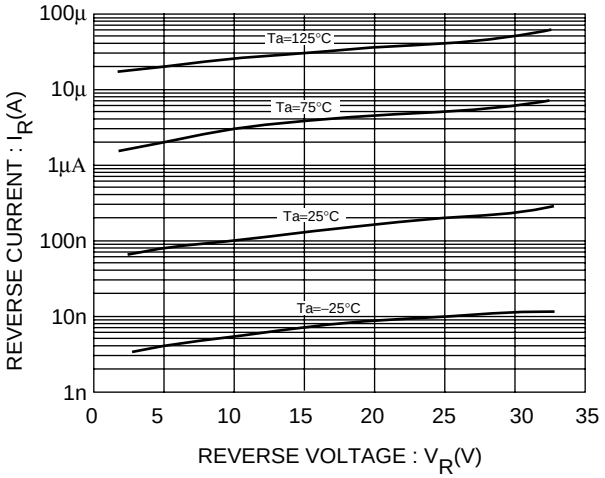


Fig. 2 Reverse characteristics

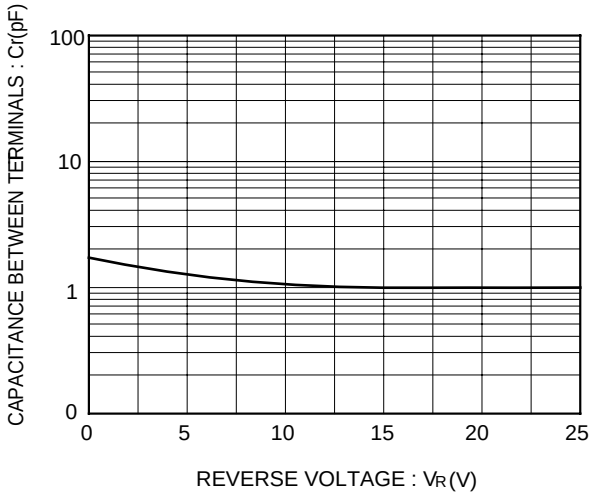


Fig. 3 Capacitance between terminals characteristics

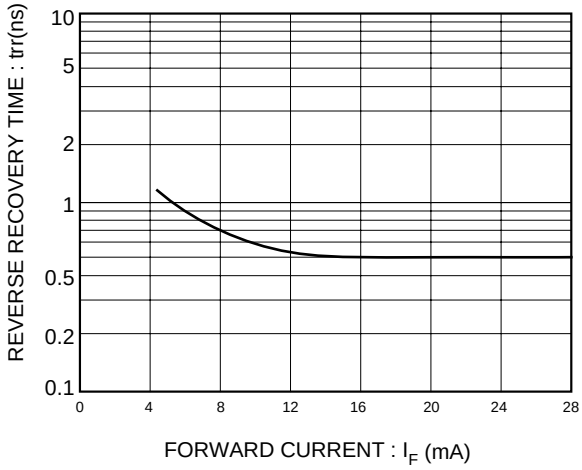
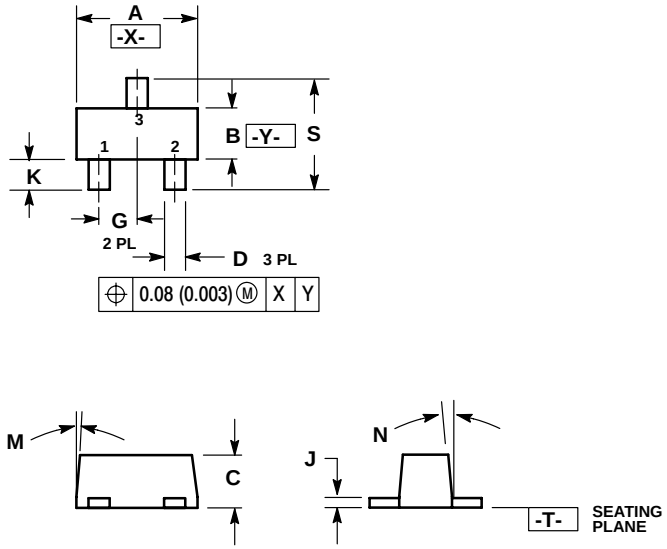


Fig. 4 Reverse recovery time characteristics

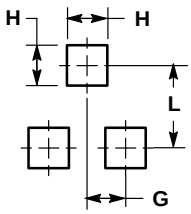
LRB715WT1

SC–89



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067



RECOMMENDED PATTERN OF SOLDER PADS